

Ultra-Large Area InGaAs p-i-n Photodiode

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35PD5M-T0

The 35PD5M-T0, an InGaAs photodiode with a 5mm-diameter photosensitive, designed for applications in high sensitivity instrumentation and sensing. Class A devices feature very low dark current and high dynamic impedance. High reliability is achieved through planar semiconductor design, dielectric-passivation, and hermetic packaging in TO-8 headers. Chips can also be attached and wire bonded to customer-supplied or other specified packages.



Features:

- Planar Structure
- Dielectric Passivation
- 100% Purge Burn-in
- High Responsivity

DEVICE CHARACTERISTICS

Parameters	Test Conditions	Minimum	Typical	Maximum	Units
Dark Current	Class A -0.3V		0.1		uA
Responsivity	1300nm		0.9		A/W
Responsivity	1500nm		0.9		A/W
Rise/Fall			1		us
Dynamic Impedance	Class A (0V)		1.2		K Ohms
Dynamic Impedance	Class B		10		K Ohms
NEP	Class A		2×10^{-13}		WHz ^{-1/2}
NEP	Class B		6×10^{-13}		WHz ^{-1/2}
D*	Class A		2×10^{12}		cmHz ^{1/2} W ⁻¹
D*	Class B		6×10^{11}		cmHz ^{1/2} W ⁻¹

ABSOLUTE MAXIMUM RATINGS

Reverse Voltage	1 Volts
Forward Current	200 mA
Reverse Current	30 mA
Operating Temperature	-40°C to +85°C
Storage Temperature	-40°C to +85°C
Soldering Temperature	250°C

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